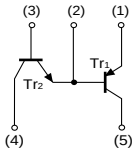
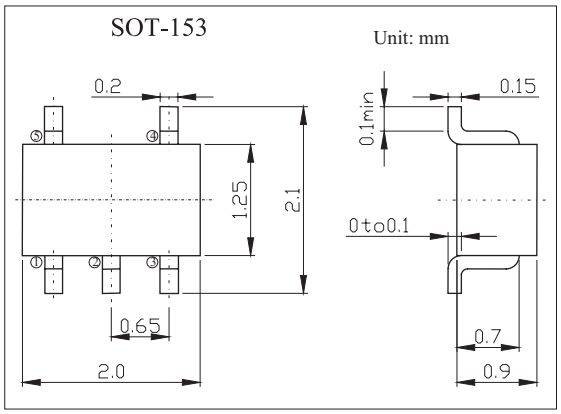
Power Management(Dual Transistors)
FMY4A

■ Features

- Collector-emitter voltage: Tr_1=-50V,Tr_2=50V
- Collector current: Tr_1=-150mA,Tr_2=150mA





■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating		Unit
		Tr1	Tr2	
Collector-base voltage	V_{CBO}	-60	60	V
Collector-emitter voltage	V_{CEO}	-50	50	V
Emitter-base voltage	V_{EBO}	-6	7	V
Collector current	I_C	-150	150	mA
Power dissipation(Total)	P_D	300		mW
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150		℃

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Transistor Tr1						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = -50 μA, I_E = 0	-60			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = -1 mA, I_B = 0	-50			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_C = -50 μA, I_C = 0	-6			V
Collector cutoff current	I_{CBO}	V_{CB}=-60V, I_E=0			-100	nA
Emitter cutoff current	I_{EBO}	V_{EB}=-6V, I_C=0			-100	nA
DC current gain	h_{FE}	V_{CE}=-6V, I_C= -1mA	120		560	
collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C = -50 mA; I_B = -5 mA			-0.5	V
Transition frequency	f_T	I_C = -2 mA; V_{CE} = -12 V; f = 100 MHz		140		MHz
Collector output capacitance	C_{ob}	V_{CB}=-12V, I_E=0A, f=1MHz			5	pF
Transistor Tr2						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 50 μA, I_E = 0	60			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1 mA, I_B = 0	50			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_C = 50 μA, I_C = 0	7			V
Collector cutoff current	I_{CBO}	V_{CB}=60V, I_E=0			100	nA
Emitter cutoff current	I_{EBO}	V_{EB}=7V, I_C=0			100	nA
DC current gain	h_{FE}	V_{CE}=6V, I_C= 1mA	120		560	
collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C = 50 mA; I_B = 5 mA			0.4	V
Transition frequency	f_T	I_C = 2 mA; V_{CE} = 12 V; f = 100 MHz		180		MHz
Collector output capacitance	C_{ob}	V_{CB}=12V, I_E=0A, f=1MHz			3.5	pF

* pulse test: Pulse Width ≤300μs, Duty Cycle≤ 2.0%.

■ Marking

Marking	Y4

■ Typical Characteristics

Tr1 (PNP)

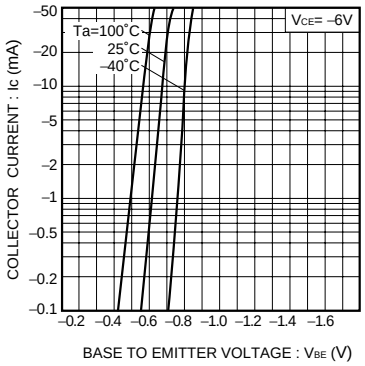

Fig.1 Grounded emitter propagation characteristics

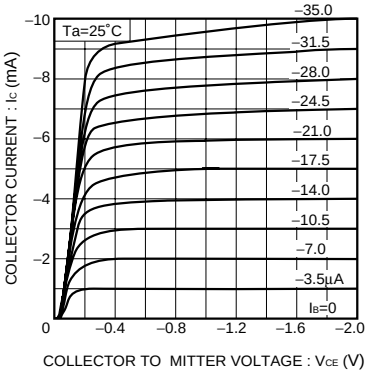

Fig.2 Grounded emitter output characteristics (I)

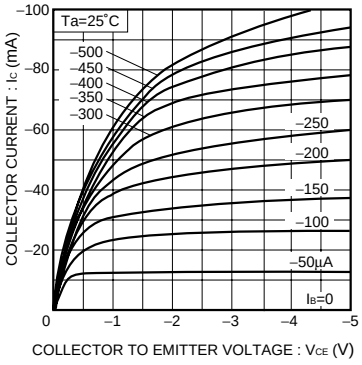

Fig.3 Grounded emitter output characteristics (II)

FMY4A

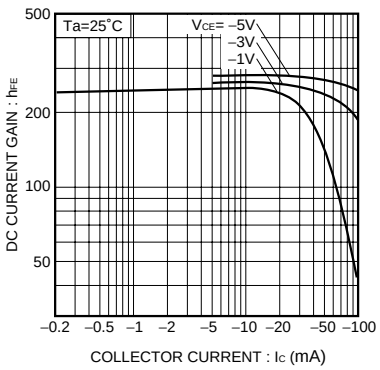

Fig.4 DC current gain vs. collector current (I)

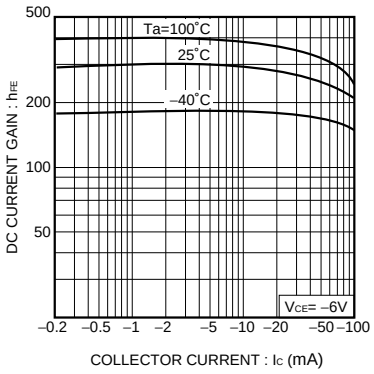

Fig.5 DC current gain vs. collector current (II)

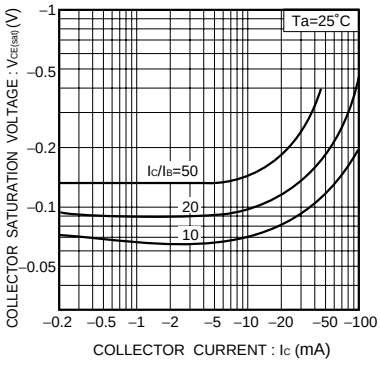

Fig.6 Collector-emitter saturation voltage vs. collector current (I)

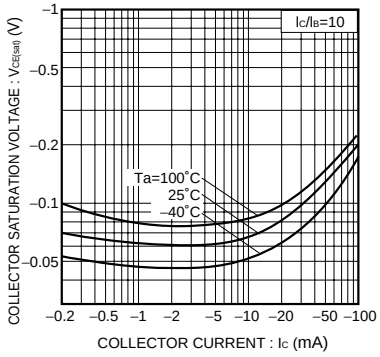

Fig.7 Collector-emitter saturation voltage vs. collector current (II)

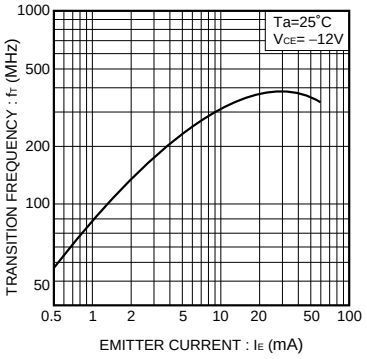

Fig.8 Gain bandwidth product vs. emitter current

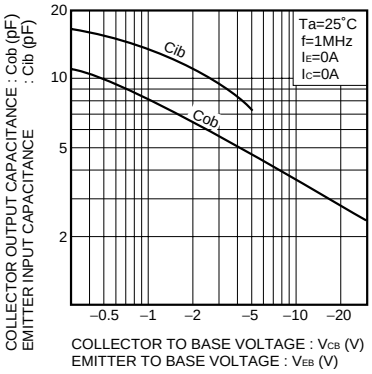

Fig.9 Collector output capacitance vs. collector-base voltage
Emitter inputcapacitance vs. emitter-base voltage

NPN Tr

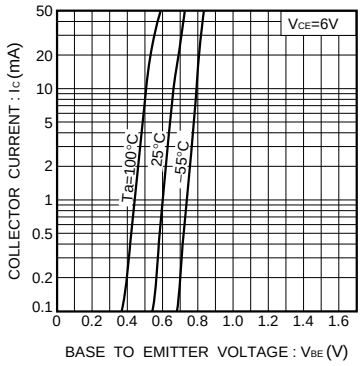

Fig.10 Grounded emitter propagation characteristics

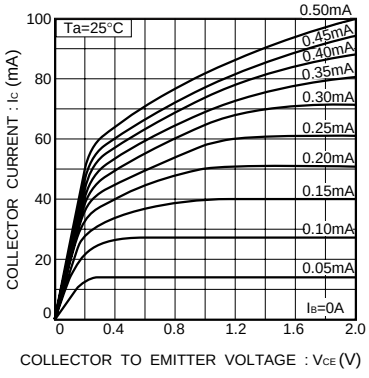

Fig.11 Grounded emitter output characteristics (I)

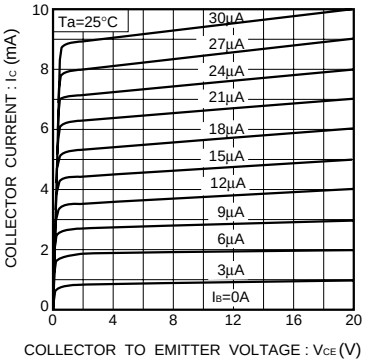

Fig.12 Grounded emitter output characteristics (II)

FMY4A

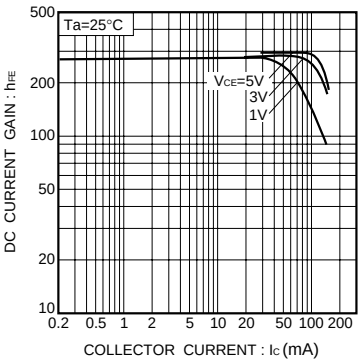

Fig.13 DC current gain vs. collector current (I)

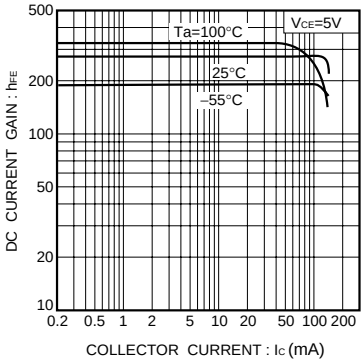

Fig.14 DC current gain vs. collector current (II)

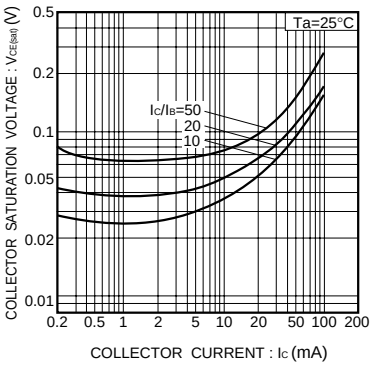

Fig.15 Collector-emitter saturation voltage vs. collector current

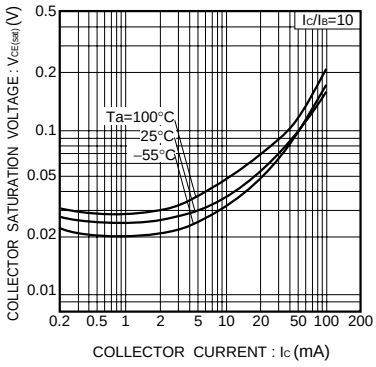

Fig.16 Collector-emitter saturation voltage vs. collector current (I)

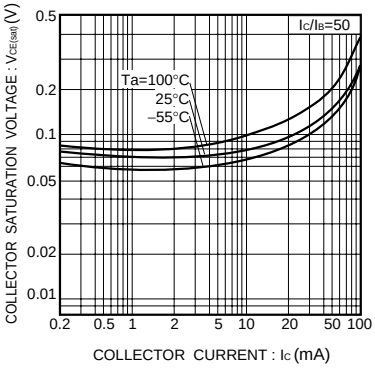

Fig.17 Collector-emitter saturation voltage vs. collector current (II)

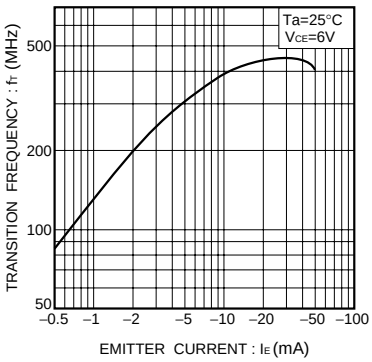

Fig.18 Gain bandwidth product vs. emitter current

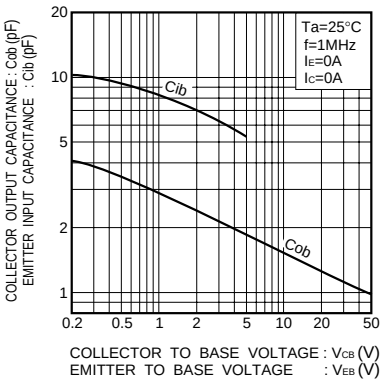

Fig.19 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

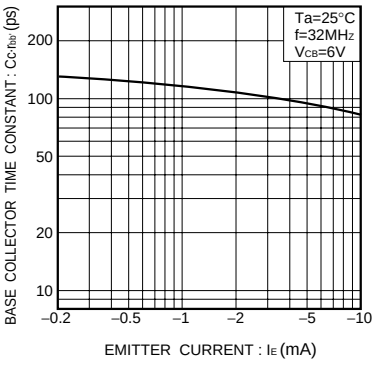

Fig.20 Base-collector time constant vs. emitter current